

IN THE CLAIMS:

Please cancel claims 1-8 and 10-13 without prejudice.

1. (Cancelled)

2. (Cancelled)

3. (Cancelled)

4. (Cancelled)

5. (Cancelled)

6. (Cancelled)

7. (Cancelled)

8. (Cancelled)

9. (Previously Presented) An apparatus for processing a substrate, comprising:
a chamber having a first electrode disposed therein;
a substrate support disposed in the chamber and providing a second electrode in the chamber;
a high frequency power source electrically connected to either the first or second electrode;
a low frequency power source electrically connected to either the first or second electrode; and
one or more variable impedance elements connected to the first and/or second electrode, wherein each variable impedance element is disposed between the first and/or second electrode and an electrical ground, wherein the variable impedance

elements are adapted to tune a self bias voltage division between the first and second electrodes.

10. (Cancelled)

11. (Cancelled)

12. (Cancelled)

13. (Cancelled)

14. (Original) An apparatus for delivering power to a process chamber having a first electrode and a substrate support forming a second electrode, comprising:
a high frequency power source electrically connected to the first electrode;
a low frequency power source electrically connected to the first electrode; and
a variable impedance element connected between the substrate support and an electrical ground.

15. (Original) The apparatus of claim 14, wherein the high frequency power source is adapted to deliver power between about 13.56 MHz and about 500 MHz.

16. (Original) The apparatus of claim 14, wherein the low frequency power source is adapted to deliver power between about 100 kHz and about 4 MHz.

17. (Original) The apparatus of claim 14, wherein the variable impedance element comprises at least one inductor and at least one capacitor.

18. (Original) The apparatus of claim 14, wherein the variable impedance element comprises at least one inductor and at least one variable capacitor.

19. (Previously Presented) An apparatus for delivering power to a process chamber having a first electrode and a substrate support forming a second electrode, comprising:

- a high frequency power source electrically connected to the first electrode;
- a low frequency power source electrically connected to the first electrode; and
- a variable impedance element connected between the substrate support and an electrical ground, wherein the variable impedance element is adapted to tune a self bias voltage division between the first electrode and the substrate support.

20. (Original) The apparatus of claim 14, wherein the variable impedance element is adapted to tune at least one resonant impedance at a frequency selected from at least one of the low frequency and the high frequency.

21. (Original) The apparatus of claim 14, wherein the variable impedance element is adapted to tune a first resonant impedance at the low frequency and a second resonant impedance at the high frequency.

22. (Original) The apparatus of claim 14, wherein the first electrode comprises a gas distributor.

23. (Original) The apparatus of claim 14, wherein the first electrode and the substrate support are disposed to form parallel plate electrodes.

24. (Original) The apparatus of claim 14, wherein the chamber is configured as an etch chamber.